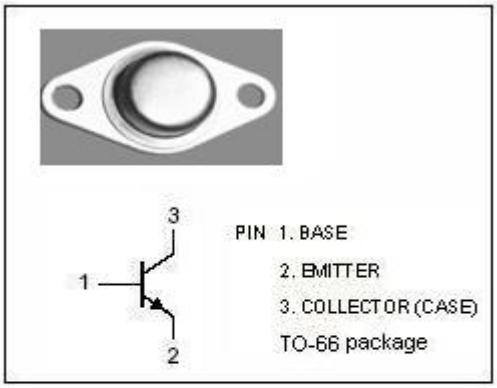
isc Silicon NPN Power Transistor 2SD157

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 300V(Min)
- Low Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= 2.0V(Max) @I_C= 50mA
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

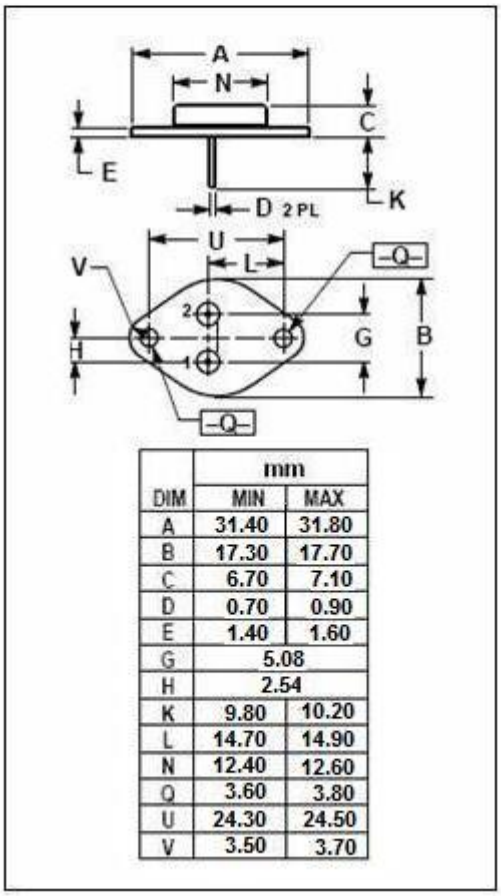


APPLICATIONS

- Designed for use in line-operated color TV chroma output circuits and sound output circuits.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	100	mA
P_C	Collector Power Dissipation @ T_C=70℃	4	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 5mA; I_B= 0	300			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 100 μ A; I_E= 0	300			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 100 μ A; I_C= 0	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 50mA; I_B=5mA			2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 50mA; I_B=5mA			2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 300V; I_E= 0			100	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= 7V; I_C= 0			10	μ A
h_{FE}	DC Current Gain	I_C= 50mA ; V_{CE}= 10V	40		200	
h_{FE-2}	DC Current Gain	I_C= 2A; V_{CE}= 2V	20			
f_T	Current-Gain—Bandwidth Product	I_C= 50mA; V_{CE}= 10V;f_{test}= 1.0MHz		20		MHz